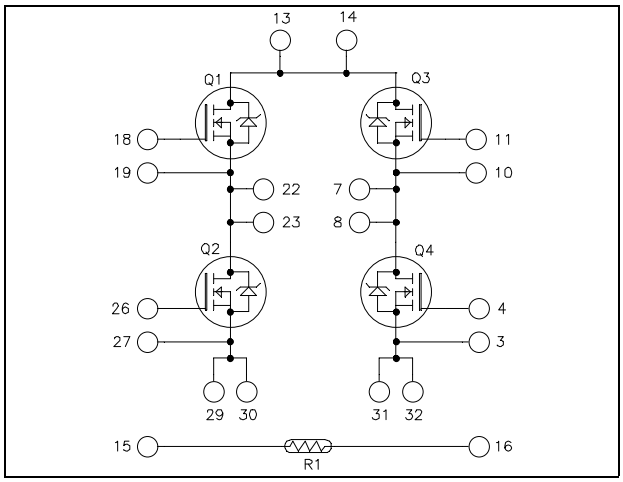
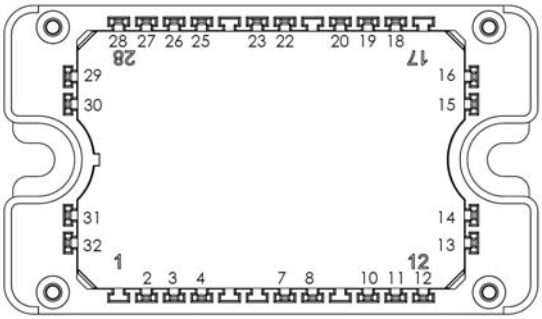
APTC80H29T3G

Full - Bridge
Super Junction MOSFET
Power Module

V_{DSS} = 800V
R_{DSon} = 290mΩ max @ Tj = 25°C
I_D = 15A @ Tc = 25°C





All multiple inputs and outputs must be shorted together
Example: 13/14 ; 29/30 ; 22/23 …

Application

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies

Features

- **Super junction MOSFET**
  - Ultra low R_{DSon}
  - Low Miller capacitance
  - Ultra low gate charge
  - Avalanche energy rated
  - Very rugged
- Kelvin source for easy drive
- Very low stray inductance
- Internal thermistor for temperature monitoring

Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- Each leg can be easily paralleled to achieve a phase leg of twice the current capability
- RoHS Compliant

All ratings @ T_j = 25°C unless otherwise specified

Absolute maximum ratings (per super junction MOSFET)

Symbol	*Parameter*		*Max ratings*	*Unit*
V_{DSS}	Drain - Source Voltage		800	V
I_D	Continuous Drain Current	T_c = 25°C	15	A
		T_c = 80°C	11	
I_{DM}	Pulsed Drain current		60	
V_{GS}	Gate - Source Voltage		±30	V
R_{DSon}	Drain - Source ON Resistance		290	mΩ
P_D	Power Dissipation	T_c = 25°C	156	W
I_{AR}	Avalanche current (repetitive and non repetitive)		17	A
E_{AR}	Repetitive Avalanche Energy		0.5	mJ
E_{AS}	Single Pulse Avalanche Energy		670	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

Electrical Characteristics (per super junction MOSFET)

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
I_{DSS}	Zero Gate Voltage Drain Current	V_{GS} = 0V,V_{DS} = 800V			25	µA
$R_{DS(on)}$	Drain – Source on Resistance	V_{GS} = 10V, I_D = 7.5A			290	mΩ
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS} = V_{DS}, I_D = 1mA	2.1	3	3.9	V
I_{GSS}	Gate – Source Leakage Current	V_{GS} = ±20 V, V_{DS} = 0V			±100	nA

Dynamic Characteristics (per super junction MOSFET)

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
C_{iss}	Input Capacitance	V_{GS} = 0V V_{DS} = 25V f = 1MHz		2254		pF
C_{oss}	Output Capacitance			1046		
C_{rss}	Reverse Transfer Capacitance			54		
Q_g	Total gate Charge	V_{GS} = 10V V_{Bus} = 400V I_D = 15A		90		nC
Q_{gs}	Gate – Source Charge			11		
Q_{gd}	Gate – Drain Charge			45		
$T_{d(on)}$	Turn-on Delay Time	**Inductive switching @125°C** V_{GS} = 15V V_{Bus} = 533V I_D = 15A R_G = 5Ω		10		ns
T_r	Rise Time			13		
$T_{d(off)}$	Turn-off Delay Time			83		
T_f	Fall Time			35		
E_{on}	Turn-on Switching Energy	**Inductive switching @ 25°C** V_{GS} = 15V, V_{Bus} = 533V I_D = 15A, R_G = 5Ω		243		µJ
E_{off}	Turn-off Switching Energy			139		
E_{on}	Turn-on Switching Energy	**Inductive switching @ 125°C** V_{GS} = 15V, V_{Bus} = 533V I_D = 15A, R_G = 5Ω		425		µJ
E_{off}	Turn-off Switching Energy			171		
R_{thJC}	Junction to Case Thermal Resistance				0.80	°C/W

Source - Drain diode ratings and characteristics (per super junction MOSFET)

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
I_S	Continuous Source current (Body diode)		Tc = 25°C		15		A
			Tc = 80°C		11		
V_{SD}	Diode Forward Voltage	V_{GS} = 0V, I_S = - 15A				1.2	V
dv/dt	Peak Diode Recovery ❶					6	V/ns
t_{rr}	Reverse Recovery Time	I_S = - 15A ; V_R = 400V di_S/dt = 100A/µs			550		ns
Q_{rr}	Reverse Recovery Charge				15		µC

❶ dv/dt numbers reflect the limitations of the circuit rather than the device itself.
$I_S \le$ - 15A di/dt ≤ 100A/µs $V_R \le V_{DSS}$ $T_j \le$ 150°C

Thermal and package characteristics

Symbol	Characteristic			Min	Max	Unit
V_{ISOL}	RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz			4000		V
T_J	Operating junction temperature range			-40	150	°C
T_{JOP}	Recommended junction temperature under switching conditions			-40	$T_J$max -25	
T_{STG}	Storage Temperature Range			-40	125	
T_C	Operating Case Temperature			-40	125	
Torque	Mounting torque	To heatsink	M4	2	3	N.m
Wt	Package Weight				110	g

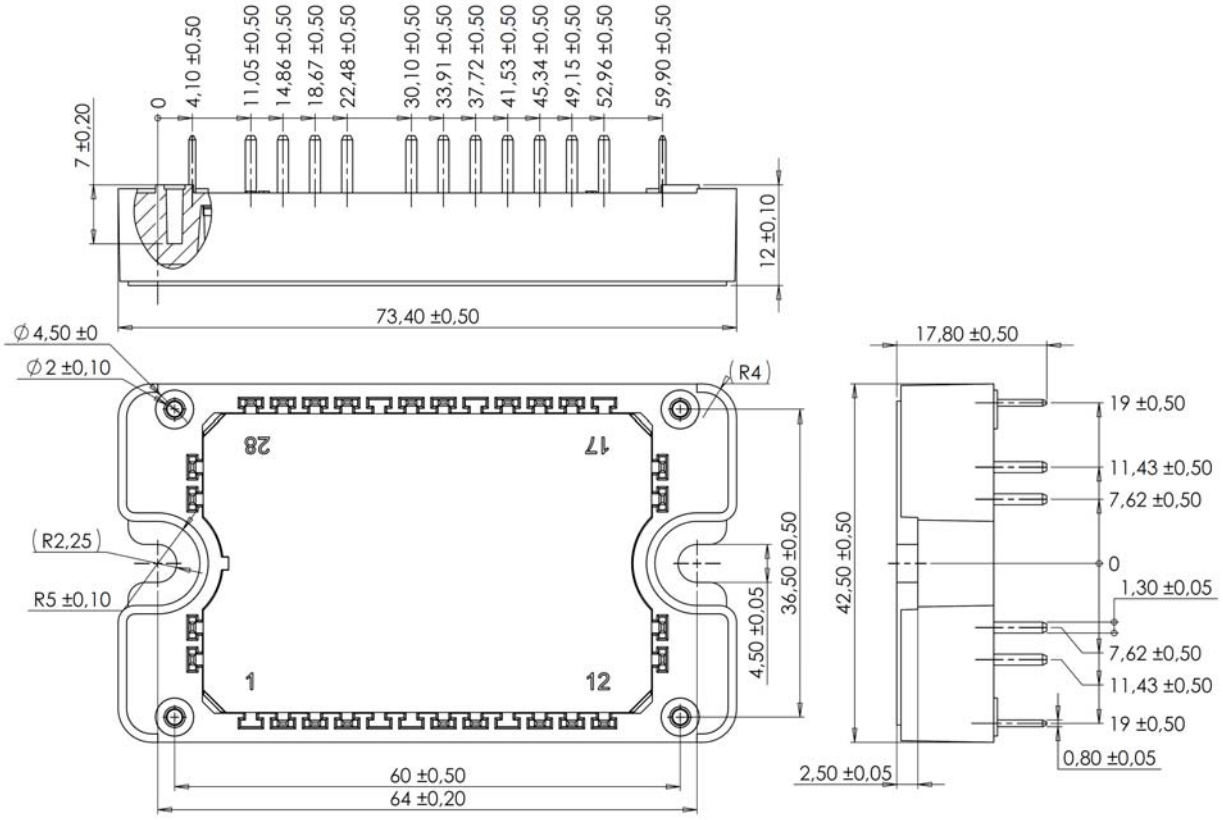
Temperature sensor NTC (see application note APT0406 on www.microsemi.com for more information).

Symbol	Characteristic		Min	Typ	Max	Unit
R_{25}	Resistance @ 25°C			50		kΩ
$\Delta R_{25}/R_{25}$				5		%
$B_{25/85}$	T_{25} = 298.15 K			3952		K
$\Delta B/B$		T_C=100°C		4		%

$$R_T = \frac{R_{25}}{\exp\left[B_{25/85}\left(\frac{1}{T_{25}} - \frac{1}{T}\right)\right]}$$

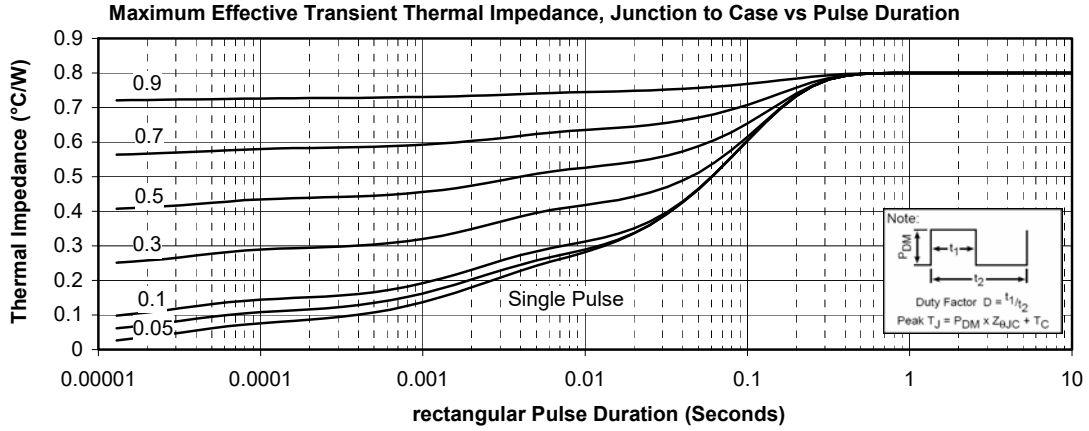
T: Thermistor temperature
R_T: Thermistor value at T

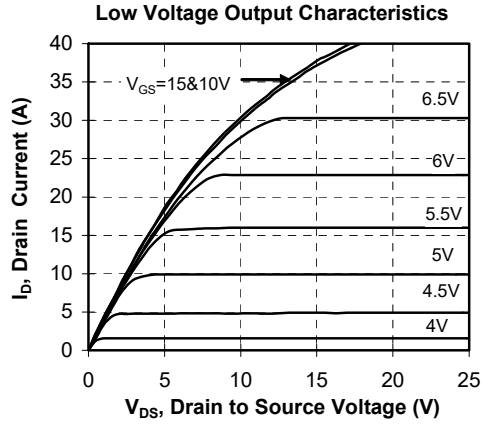
Package outline (dimensions in mm)

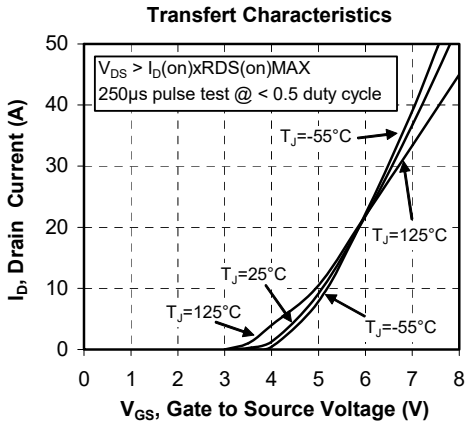


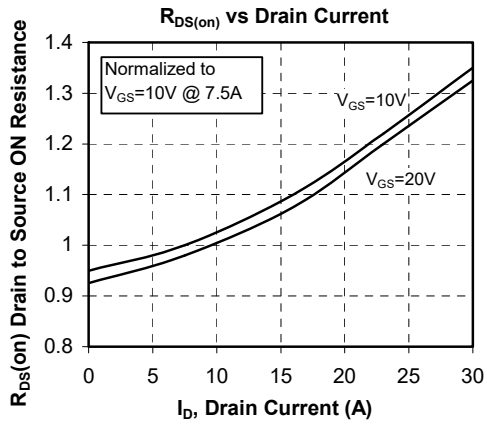
See application note 1906 - Mounting Instructions for SP3F Power Modules on www.microsemi.com

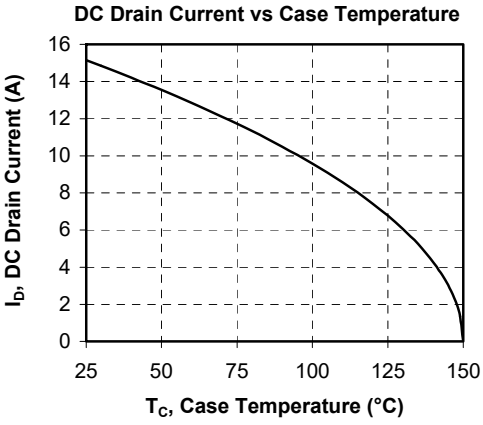
Typical performance Curve



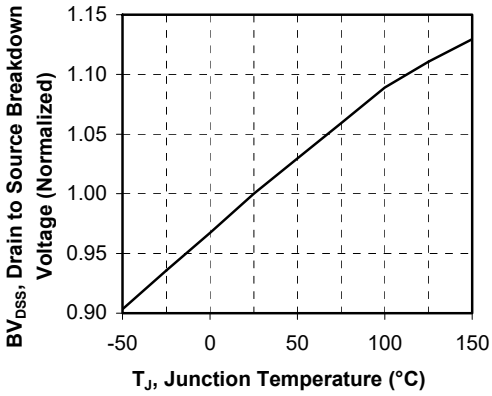




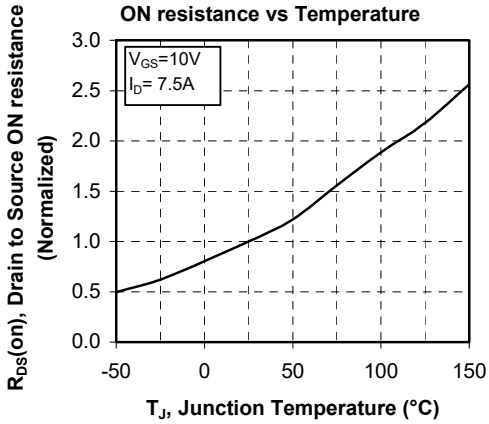




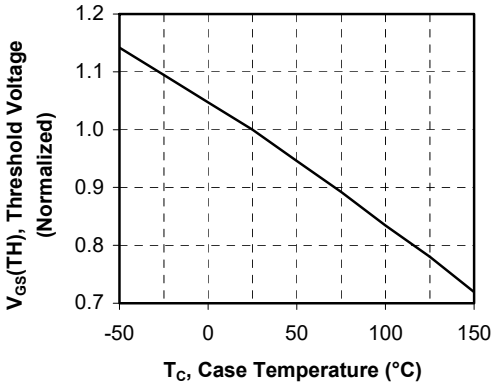
Breakdown Voltage vs Temperature



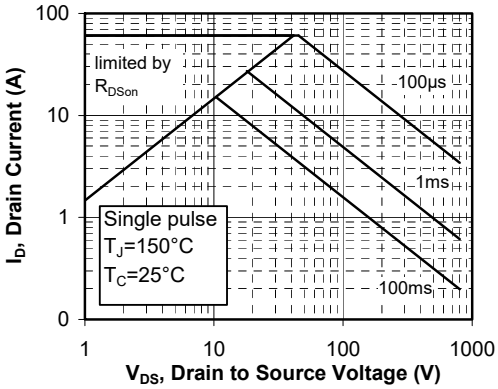
ON resistance vs Temperature



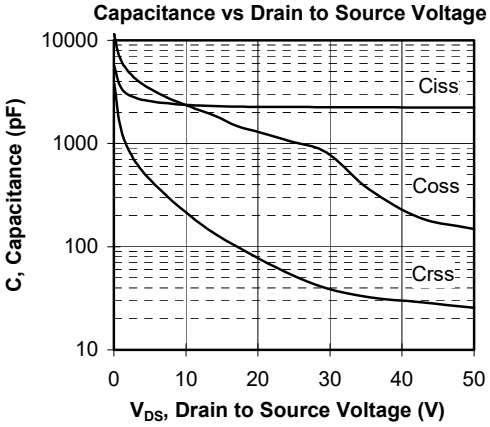
Threshold Voltage vs Temperature



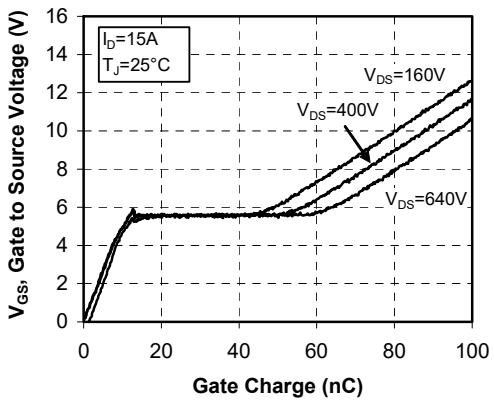
Maximum Safe Operating Area



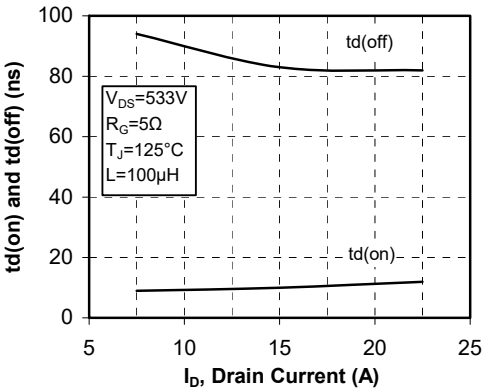
Capacitance vs Drain to Source Voltage



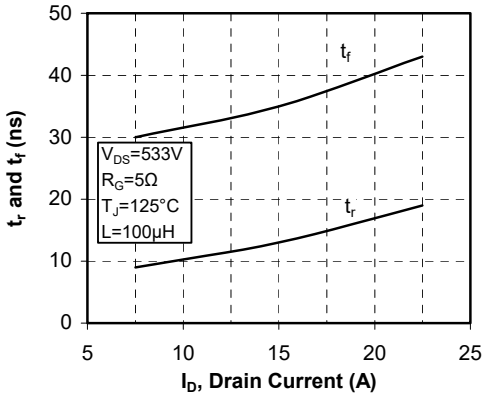
Gate Charge vs Gate to Source Voltage



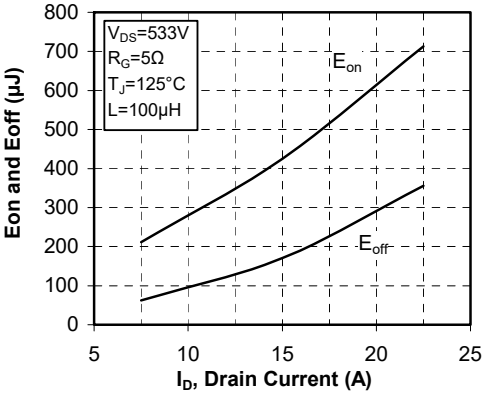
Delay Times vs Current



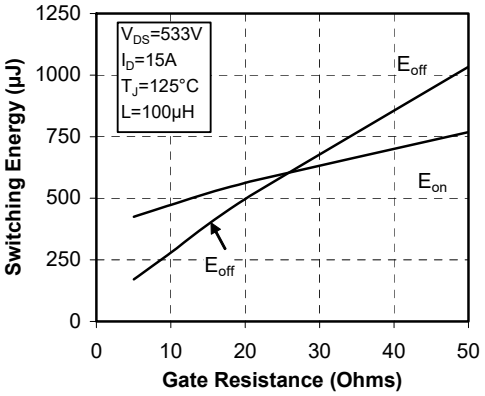
Rise and Fall times vs Current



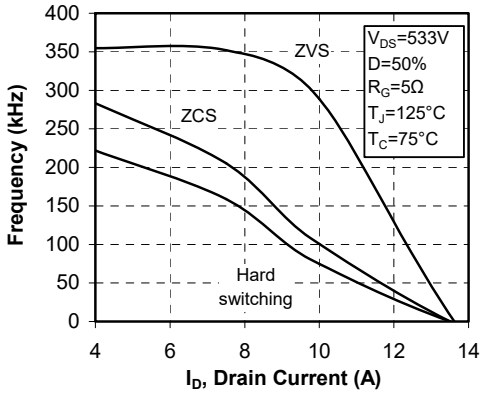
Switching Energy vs Current



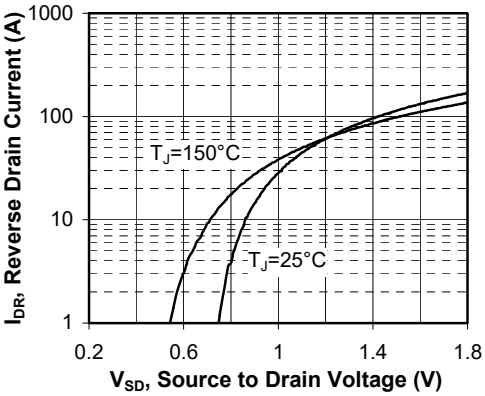
Switching Energy vs Gate Resistance



Operating Frequency vs Drain Current



Source to Drain Diode Forward Voltage



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